

# **isc Silicon NPN Power Transistor**

#### **DESCRIPTION**

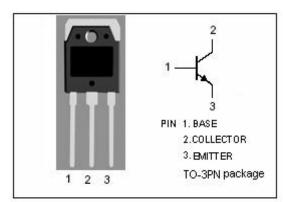
- · High Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= 500V(Min)
- · High Switching Speed
- · Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

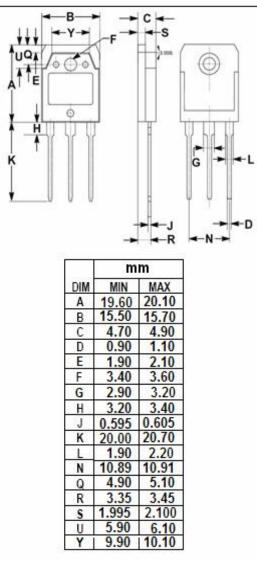
### **APPLICATIONS**

 Designed for ultrahigh-definition CRT display horizontal deflection output applications.

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	900	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	500	V	
V <sub>EBO</sub>	Emitter-Base voltage	7	V	
Ic	Collector Current-Continuous	7	А	
Ісм	Collector Current-Peak	14	А	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C	80	W	
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	







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2SC3636

### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	500			V			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.8A			2.0	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.8A			1.5	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V; I <sub>E</sub> = 0			10	μА			
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 900V; R <sub>BE</sub> = 0			0.5	mA			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			1	mA			
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.8A; V <sub>CE</sub> = 5V	8						
Switching Times									
tstg	Storage Time				3.0	μ <b>S</b>			
t <sub>f</sub>	Fall Time	I <sub>C</sub> = 4A, I <sub>B1</sub> = 0.8A; I <sub>B2</sub> = -1.6A			0.2	μs			

tstg	Storage Time	- I <sub>C</sub> = 4A, I <sub>B1</sub> = 0.8A; I <sub>B2</sub> = -1.6A		3.0	μς
t <sub>f</sub>	Fall Time			0.2	μS

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